Electronic Supplementary Material (ESI) for Materials Advances.

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Supplementary Information

Photo-enhanced Metal-assisted Chemical Etching of α-Gallium Oxide Grown by Halide Vapor-Phase Epitaxy on a Sapphire Substrate and its Applications

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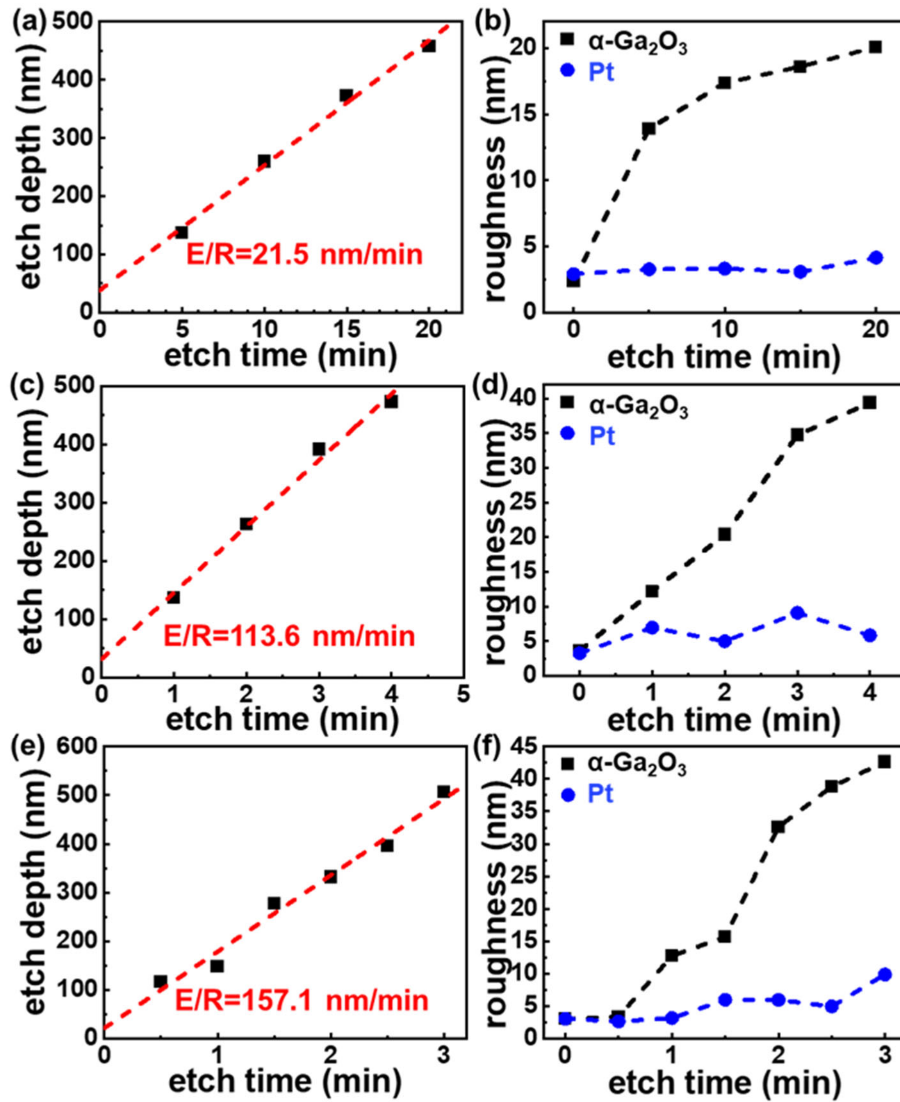

Figure S1. (a) Etch rate (E/R) of PE-MAC etch of α-Ga_2O_3 at 32 ℃. (b) RMS roughness changes at 32 ℃ etching. (c) Etch rate (E/R) of PE-MAC etch of α-Ga_2O_3 at 45 ℃. (d) RMS roughness changes in 45 ℃ etching. (e) Etch rate (E/R) of PE-MAC etch of α-Ga_2O_3 at 50 ℃. (f) RMS roughness changes in 50 ℃ etching.

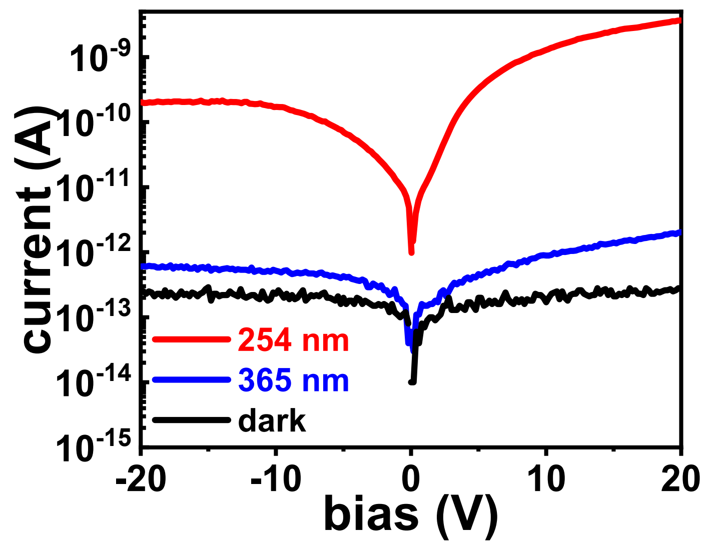

Figure S2. *I–V* characteristics of α-Ga_2O_3 PD under dark condition as well as 254 and 365 nm lights illuminations.